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November 2013

FQP19N20C / FQPF19N20C

N-Channel QFET® MOSFET

200 V, 19 A, 170 mΩ

Features

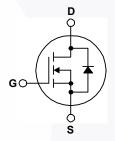
- 19 A, 200 V, $R_{DS(on)}$ = 170 m Ω (Max.) @ V_{GS} = 10 V, I_D = 9.5 A
- Low Gate Charge (Typ. 40.5 nC)
- Low Crss (Typ. 85 pF)
- · 100% Avalanche Tested

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.







MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FQP19N20C	FQPF19N20C	Unit	
V _{DSS}	Drain to Source Voltage		200		V	
I _D	Drain Current	-Continuous (T _C = 25°C)	-Continuous (T _C = 25°C)		19.0 *	Α
	Drain Current	-Continuous (T _C = 100°C)	-Continuous (T _C = 100°C)		12.1 *	Α
I _{DM}	Drain Current	- Pulsed	(Note 1)	76.0	76.0 *	Α
V _{GSS}	Gate to Source Voltage			± 30		V
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	433		mJ
I _{AR}	Avalanche Current		(Note 1)	19.0		Α
E _{AR}	Repetitive Avalanche Energy		(Note 1)	13.9		mJ
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	5.5		V/ns
P_{D}	Power Dissipation	(T _C = 25°C)		139	43	W
	- Derate above 25°C			1.11	0.34	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C	
T _L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds			300		°C

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FQP19N20C	FQPF19N20C	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max	0.9	2.89	°C/W
$R_{\theta JA}$	JA Thermal Resistance, Junction to Ambient, Max		62.5	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FQP19N20C	FQP19N20C	TO-220	Tube	N/A	50 units
FQPF19N20C	FQPF19N20C	TO-220F	Tube	N/A	50 units

Electrical Characteristics T_C = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	aracteristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	200			V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.24		V/°C
I _{DSS} Zero Gate Voltage	Zana Oaka Malka wa Danin Ouwant	V _{DS} = 200 V, V _{GS} = 0 V			10	μА
	ro Gate Voltage Drain Current	V _{DS} = 160 V, T _C = 125°C			100	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward V _{GS} = 30 V, V _{DS} = 0 V				100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Cha	racteristics					
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μA	2.0		4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 9.5 A	\-	0.14	0.17	Ω
9 _{FS}	Forward Transconductance $V_{DS} = 40 \text{ V}, I_D = 9.5 \text{ A}$			10.8		S
•	ic Characteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$		830	1080	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		195	255	pF
C _{rss}	Reverse Transfer Capacitance			85	110	pF
Switchi	ing Characteristics					
t _{d(on)}	Turn-On Delay Time V _{DD} = 100 V, I _D = 19.0 A,			15	40	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$		150	310	ns
t _{d(off)}	Turn-Off Delay Time			135	280	ns
t _f	Turn-Off Fall Time	(Note 4)		115	240	ns
Q_g	Total Gate Charge	V _{DS} = 160 V, I _D = 19.0 A,	/	40.5	53.0	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V		6.0		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		22.5		nC
Drain-S	ource Diode Characteristics and	I Maximum Ratings				
I _S	Maximum Continuous Drain-Source Diode			19.0	Α	
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				76.0	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 19.0 A			1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 19.0 A,		208		ns
Q _{rr}	Reverse Recovery Charge dI _F / dt = 100 A/μs			1.63		μС

Notes

^{1.} Repetitive Rating : Pulse width limited by maximum junction temperature.

^{2.} L = 1.8 mH, I_{AS} = 19.0 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.

^{3.} $I_{SD} \le 19.0$ A, di/dt ≤ 300 A/ μ s, $V_{DD} \le BV_{DSS_s}$ starting T_J = 25°C.

^{4.} Essentially independent of operating temperature.

Typical Characteristics

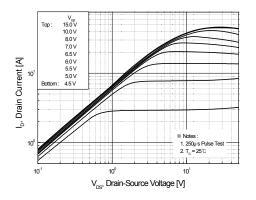


Figure 1. On-Region Characteristics

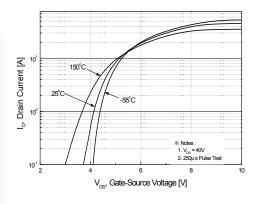


Figure 2. Transfer Characteristics

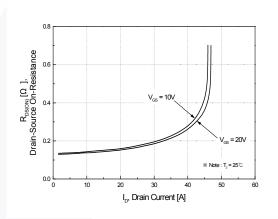


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

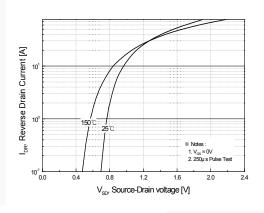


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

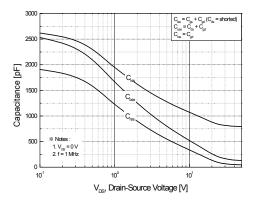


Figure 5. Capacitance Characteristics

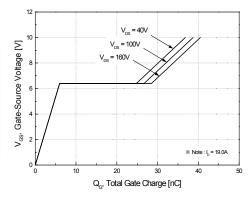


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

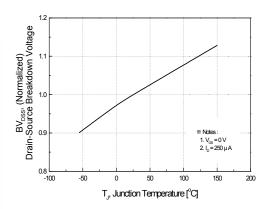


Figure 7. Breakdown Voltage Variation vs Temperature

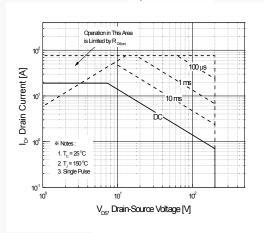


Figure 9-1. Maximum Safe Operating Area for FQP19N20C

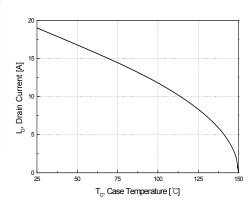


Figure 10. Maximum Drain Current vs Case Temperature

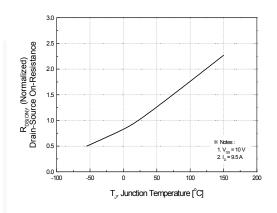


Figure 8. On-Resistance Variation vs Temperature

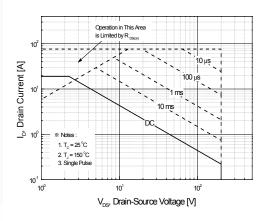


Figure 9-2. Maximum Safe Operating Area for FQPF19N20C

Typical Characteristics (Continued)

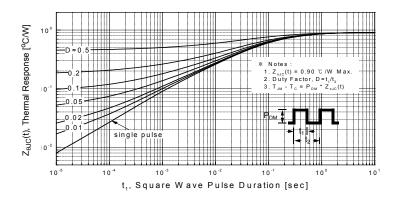


Figure 11-1. Transient Thermal Response Curve for FQP19N20C

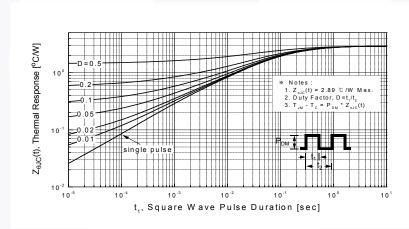


Figure 11-2. Transient Thermal Response Curve for FQPF19N20C

Figure 12. Gate Charge Test Circuit & Waveform

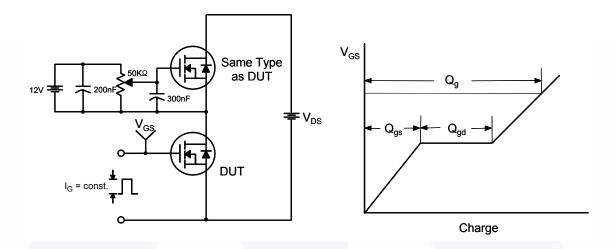


Figure 13. Resistive Switching Test Circuit & Waveforms

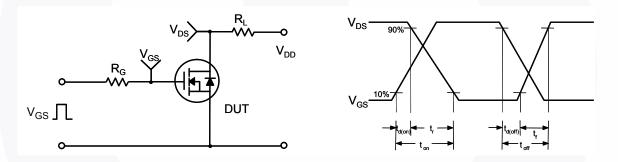
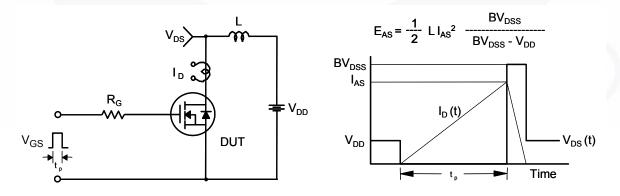


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



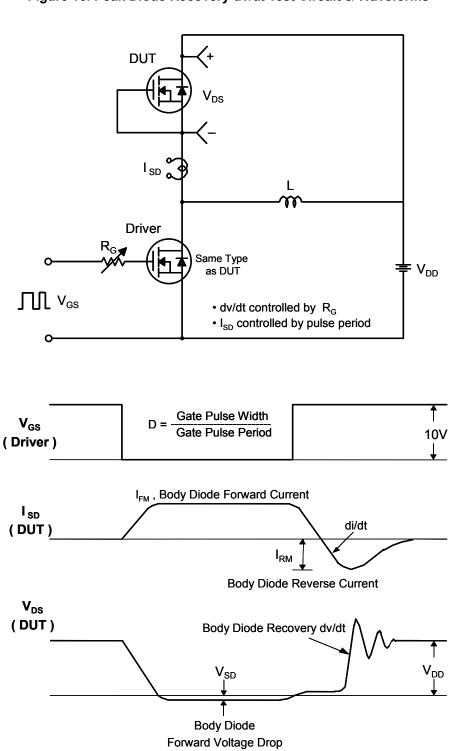


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

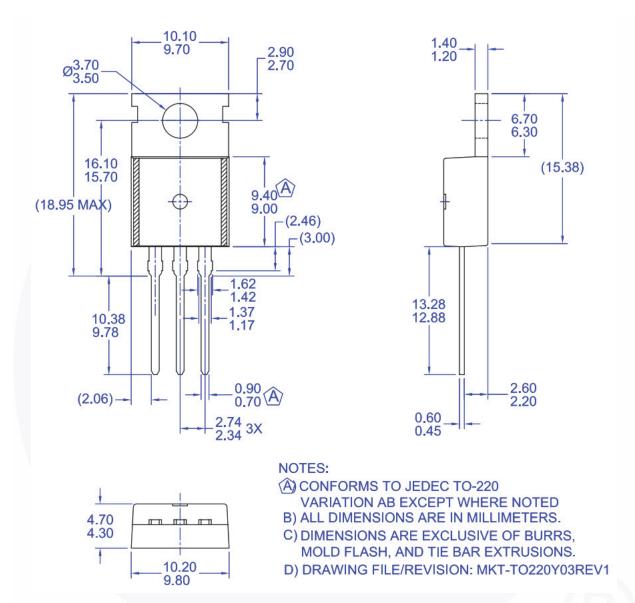


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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Mechanical Dimensions

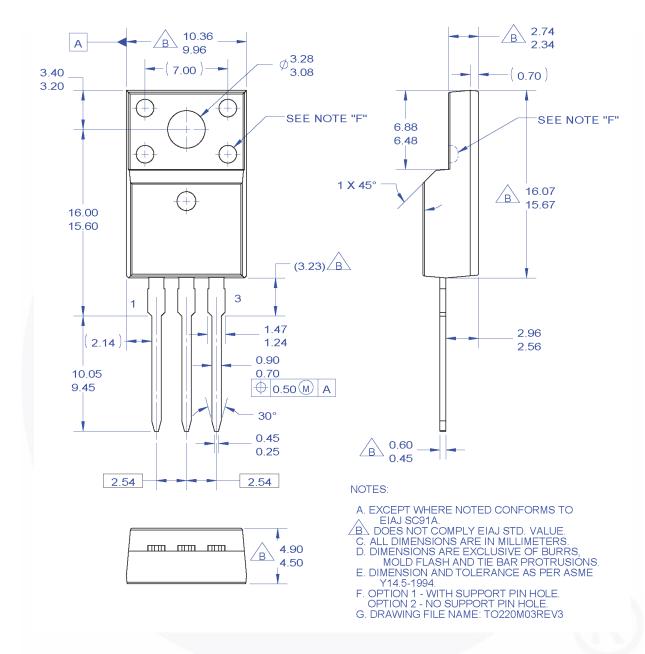


Figure 17. TO220, Molded, 3-Lead, Full Pack, EIAJ SC91, Straight Lead

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